

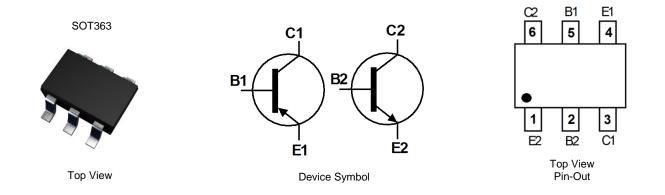
Features & Benefits

- Complementary Pairs:
 - One 2222A Type (NPN)
 - One 2907A Type (PNP)
- Ideal for Low-Power Amplification and Switching
- Totally Lead-Free & Fully RoHS compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- The MMDT2227Q is suitable for automotive applications requiring specific change control; this part is AEC-Q101 qualified, PPAP capable, and manufactured in IATF16949 certified facilities.

https://www.diodes.com/quality/product-definitions/

Mechanical Data

- Package: SOT363
- Package Material: Molded Plastic, "Green" Molding Compound UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 ^(C)
- Weight: 0.006 grams (approximate)



Ordering Information (Note 4)

Orderable Part Number	Marking	Reel size (inches) Tape width		Pack	ing
Orderable Fart Number	Marking	Reel Size (Inches)	Tape width (mm)	Quantity	Carrier
MMDT2227Q-7-F	K27	7	8	3,000	Reel

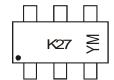
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



K27 = Product Type Marking Code YM = Date Code Marking Y or \overline{Y} = Year (ex: K = 2023) M or \overline{M} = Month (ex: 2 = February)

Date Code Key

Year	2022	2023	2024	2025	2026	2027	2028	2029	2030	2031	2032	2033
Code	J	K	L	М	Ν	0	Р	R	S	Т	U	V
Month	Jan	Feb	Mar	Apr	Мау	Jun	Jul	Aug	Sep	Oct	Nov	Dec



Maximum Ratings, 2222A Type (NPN) (@ Tamb = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	75	V
Collector-Emitter Voltage	V _{CEO}	40	V
Emitter-Base Voltage	V _{EBO}	6	V
Continuous Collector Current	Ι _C	600	mA

Maximum Ratings, 2907A Type (PNP) (@ Tamb = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-60	V
Collector-Emitter Voltage	V _{CEO}	-60	V
Emitter-Base Voltage	V _{EBO}	-6	V
Continuous Collector Current	Ι _C	-600	mA

Thermal Characteristics (@ $T_{amb} = +25^{\circ}C$, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	PD	200	mW
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{ hetaJA}$	625	
Thermal Resistance, Junction to Case	(Note 6)	$R_{ ext{ heta}JC}$	150	°C/W
Operating and Storage Temperature Range		T _J , T _{STG}	-55 to +150	°C

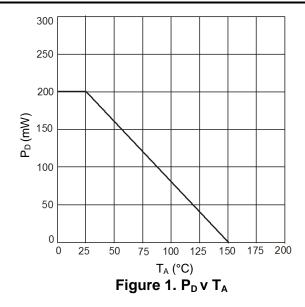
ESD Ratings (Note 7)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	ЗA
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes: 5. For the device mounted on minimum recommended pad layout FR-4, device is measured under still air conditions whilst operating in a steady-state. 6. Thermal resistance from junction to the top of package.

7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristic and Derating Information



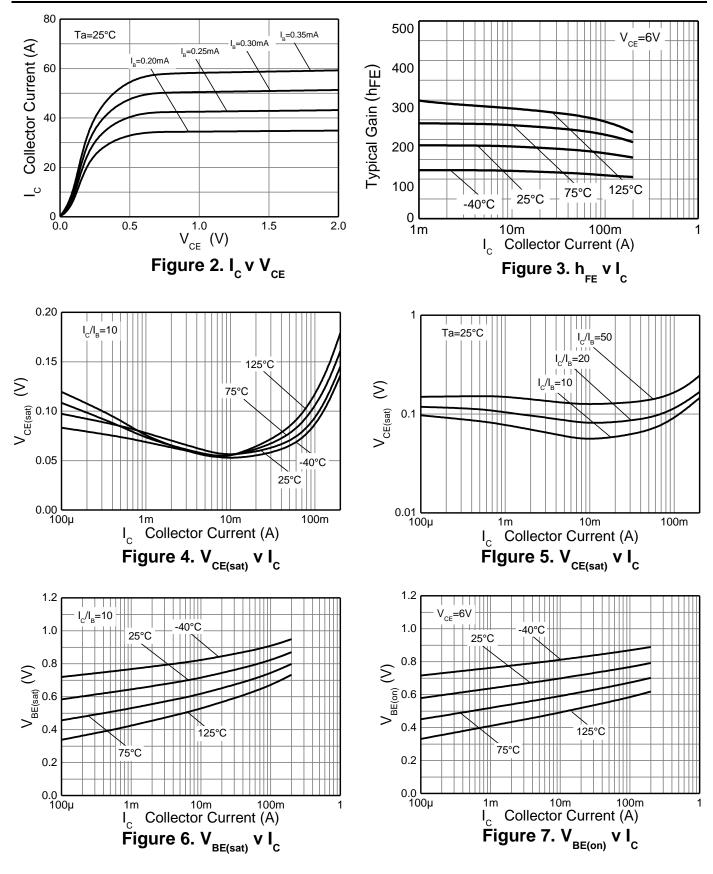


Electrical Characteristics, 2222A Type (NPN) (@ Tamb = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)					
Collector-Base Breakdown Voltage	BV _{CBO}	75		V	$I_{\rm C} = 100 \mu A$
Collector-Emitter Breakdown Voltage	BV _{CEO}	40	_	V	$I_{C} = 10 \text{mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	6.0		V	I _E = 100μA
Collector Cutoff Current	1		10	nA	$V_{CB} = 60V$
	I _{СВО}		10	μΑ	$V_{CB} = 60V, T_{amb} = +150^{\circ}C$
Collector Cutoff Current	I _{CEX}		10	nA	$V_{CE} = 60V, V_{EB(off)} = 3.0V$
Emitter Cutoff Current	I _{EBO}		10	nA	$V_{EB} = 5.0V$
Base Cutoff Current	I _{BL}	—	20	nA	$V_{CE} = 60V, V_{EB(off)} = 3.0V$
ON CHARACTERISTICS (Note 8)					
		35			$I_{C} = 100 \mu A, V_{CE} = 10 V$
		50			$I_{C} = 1mA, V_{CE} = 10V$
		75	—		$I_{C} = 10 mA, V_{CE} = 10 V$
DC Current Gain	h _{FE}	100	300		$I_{C} = 150 \text{mA}, V_{CE} = 10 \text{V}$
		40	—		$I_{C} = 500 \text{mA}, V_{CE} = 10 \text{V}$
		50	—		$I_{C} = 10mA$, $V_{CE} = 10V$, $T_{amb} = -55^{\circ}C$
		35	_		$I_{C} = 150 \text{mA}, V_{CE} = 1 \text{V}$
Collector-Emitter Saturation Voltage	V _{CE(sat)}		0.3	V	$I_{C} = 150 \text{mA}, I_{B} = 15 \text{mA}$
	VCE(sat)		1.0	v	$I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$
Base-Emitter Saturation Voltage	Varia	0.6	1.2	V	I _C = 150mA, I _B = 15mA
•	V _{BE(sat)}		2.0	v	$I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$
SMALL SIGNAL CHARACTERISTICS	•				1
Output Capacitance	Cobo	—	8	pF	$V_{CB} = 10V$, f = 1MHz
Input Capacitance	Cibo	—	25	pF	V _{EB} = 0.5V, f = 1MHz
Current Gain-Bandwidth Product	f⊤	300	—	MHz	$V_{CE} = 20V, I_C = 20mA,$ f = 100MHz
Noise Figure	NF		4.0	dB	$V_{CE} = 10V, I_C = 100\mu A,$ R _S = 1kΩ, f = 1kHz
SWITCHING CHARACTERISTICS	I	1	1	1	103 - 1032,1 - 10112
Delay Time	t _d		10	ns	$V_{CC} = 30V, I_C = 150mA,$
Rise Time	t _r		25	ns	$V_{BE(off)} = -0.5V, I_{B1} = 15mA$
Storage Time	ts		225	ns	$V_{CC} = 30V, I_C = 150mA,$
Fall Time	ts tf		60	ns	$I_{B1} = -I_{B2} = 15mA$
	ч				

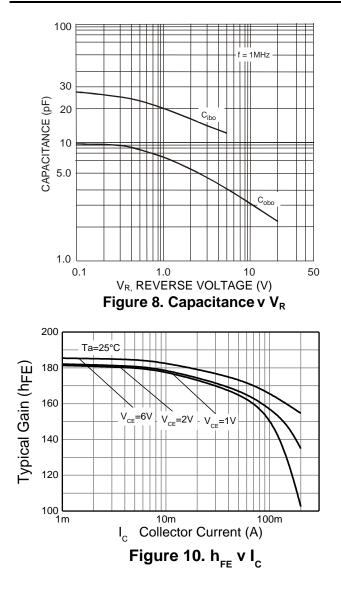
Note: 8. Pulse test: Pulse width \leq 300 μ s, duty cycle \leq 2%.

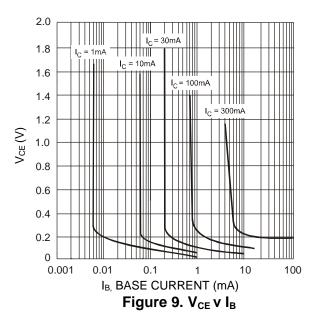




4 of 10 Downloaded From Oneyac.com







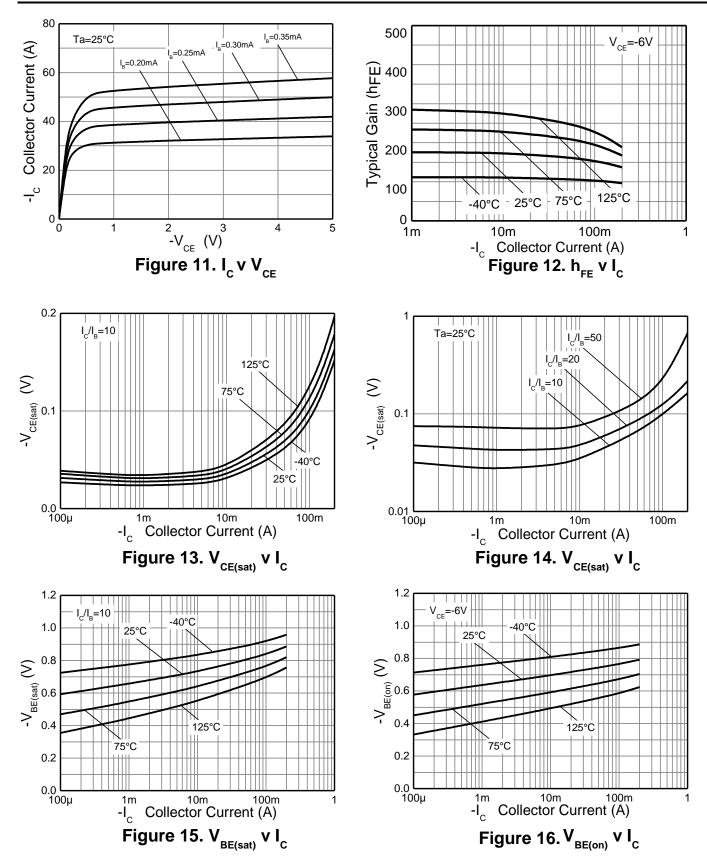


Electrical Characteristics, 2907A Type (PNP) (@T_{amb} = +25°C, unless otherwise specified.)

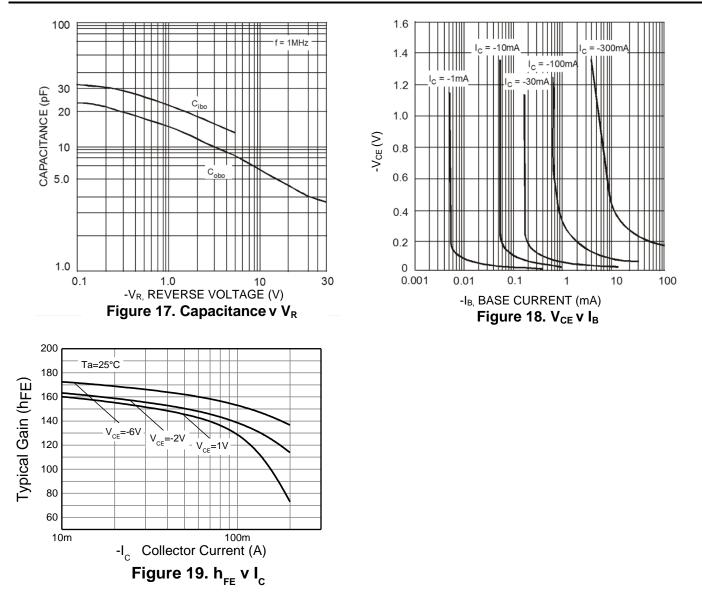
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Characteristic	Symbol	Min	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 9)	-	r			1
Collector-Base Breakdown Voltage	BV _{CBO}	-60	—	V	I _C = -100μA
Collector-Emitter Breakdown Voltage	BVCEO	-60	—	V	$I_{C} = -10 \text{mA}$
Emitter-Base Breakdown Voltage	BV _{EBO}	-6.0	—	V	I _E = -100μA
Collector Cutoff Current			-10	nA	$V_{CB} = -50V$
	I _{CBO}		-10	μA	$V_{CB} = -50V, T_{amb} = +125^{\circ}C$
Collector Cutoff Current	ICEX	_	-50	nA	$V_{CE} = -30V, V_{EB(off)} = -0.5V$
Base Cutoff Current	I _{BL}		-50	nA	$V_{CE} = -30V, V_{EB(off)} = -0.5V$
ON CHARACTERISTICS (Note 9)					
		75	_		I _C = -100μA, V _{CE} = -10V
		100	_		$I_{C} = -1.0 \text{mA}, V_{CE} = -10 \text{V}$
DC Current Gain	h _{FE}	100	_	—	I _C = -10mA, V _{CE} = -10V
		100	300		I _C = -150mA, V _{CE} = -10V
		50	—		$I_{C} = -500 \text{mA}, V_{CE} = -10 \text{V}$
Collector-Emitter Saturation Voltage			-0.4	V	I _C = -150mA, I _B = -15mA
	V _{CE(sat)}		-1.6	v	$I_{C} = -500 \text{mA}, I_{B} = -50 \text{mA}$
Base-Emitter Saturation Voltage			-1.3	V	I _C = 150mA, I _B = 15mA
Dase-Emilier Saluration voltage	V _{BE(sat)}		-2.6	v	$I_{C} = 500 \text{mA}, I_{B} = 50 \text{mA}$
SMALL SIGNAL CHARACTERISTICS					·
Output Capacitance	Cobo	—	8.0	pF	$V_{CB} = -10V, f = 1MHz$
Input Capacitance	Cibo	_	30	pF	V _{EB} = -2V, f = 1MHz
Current Gain-Bandwidth Product	f⊤	200	_	MHz	$V_{CE} = -20V, I_C = -50mA,$ f = 100MHz
SWITCHING CHARACTERISTICS					
Turn-On Time	t _{on}	_	45	ns	_
Delay Time	t _d		10	ns	$V_{CC} = -30V$, $I_{C} = -150$ mA,
Rise Time	tr		40	ns	$I_{B1} = -15 \text{mA}$
Turn-Off Time	t _{off}		100	ns	_
Storage Time	ts		80	ns	V _{CC} = -6V, I _C = -150mA,
Fall Time	t _f	_	30	ns	$I_{B1} = I_{B2} = -15 \text{mA}$

Note: 9. Short duration pulse test used to minimize self-heating effect.





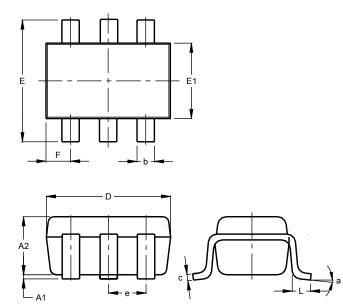






Package Outline Dimensions

Please see https://www.diodes.com/design/support/packaging/diodes-packaging/ for the latest version.

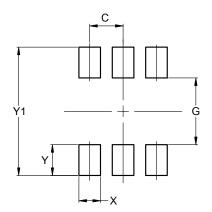


SOT363							
Dim	Min	Max	Тур				
A1	0.00	0.10	0.05				
A2	0.90	1.00	0.95				
b	0.10	0.30	0.25				
C	0.10	0.22	0.11				
D	1.80	2.20	2.15				
Е	2.00	2.20	2.10				
E1	1.15	1.35	1.30				
е	C).650 E	SC				
F	0.40	0.45	0.425				
L	0.25	0.40	0.30				
а	0°	8°					
All I	Dimen	sions	in mm				

Suggested Pad Layout

Please see https://www.diodes.com/design/support/packaging/diodes-packaging/ for the latest version.

SOT363



Dimensions	Value (in mm)
С	0.650
G	1.300
Х	0.420
Y	0.600
Y1	2.500



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